

RN2Z

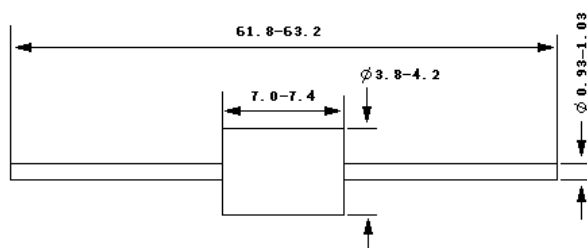
SILICON RECTIFIER DIODE Forward Current – 2.0 Ampere

Features

- For pulse rectification applications

Mechanical Data

- **Case:** Resin molded



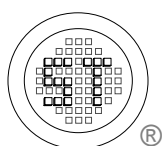
Dimensions in mm

Absolute Maximum Ratings and Characteristics

	Symbols	Rating	Units
Transient Peak Reverse Voltage	V_{RSM}	200	V
Peak Reverse Voltage	V_{RM}	200	V
Average Forward Current at $T_C = 125^\circ\text{C}$	$I_{F(AV)}$	2	A
Peak Surge Forward Current 10mS Single Half Sine	I_{FSM}	70	A
Junction Temperature	T_j	-40 to +150	$^\circ\text{C}$
Storage Temperature Range	T_s	-40 to +150	$^\circ\text{C}$

Characteristics ($T_a=25^\circ\text{C}$, unless otherwise specified)

	Symbol	Value(max.)	Unit
Forward Voltage Drop at $I_F=2\text{A}$	V_F	0.92	V
Reverse Leakage Current at $V_R=V_{RM}$	I_R	50	μA
Reverse Leakage Current Under High Temperature at $V_R=V_{RM}$, $T_j=150^\circ\text{C}$	HI_R	4	mA
Reverse Recovery Time, Recovery point 90% at $I_F=I_{RP}=100\text{mA}$	T_{rr-1}	100	nS
Reverse Recovery Time, Recovery point 75% at $I_F=100\text{mA}$, $I_{RP}=200\text{mA}$	T_{rr-2}	50	nS
Thermal Resistance Between Junction and Lead	θ_{j-1}	12	$^\circ\text{C/W}$



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
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